

FORM PTO-1449 U.S. DEPARTMENT OF
COMMERCE
(Rev. 2-32) PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
30-4687 (4790)

SERIAL NO.:

09/328,646

INFORMATION DISCLOSURE
STATEMENT BY APPLICANTAPPLICANT:
SHI-QING WANG, ET AL

(Use several sheets if necessary)

FILING DATE:

06/09/99

GROUP:

2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
V	AA	5,693,566	12/02/1997	Cheung	437	195	—
V	AB	5,864,172	01/26/1999	Kapoor, et al.	257	634	—
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	YES	NO
V	AL	0 680 085 A1	04/28/1995	02/11/95 Europe	—	—	✓		
V	AM	0 692 824 A2	07/14/1995	01/17/96 Europe	—	—	✓		
V	AN	0 805 491 A2	04/29/1997	05/11/97 Europe	—	—	✓		
V	AO	0 849 796 A2	12/16/1997	06/24/98 Europe	—	—	✓		
	AP								
	AQ								

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

V	AR	XP 000300654, Multilevel Interconnection Structure, IBM Technical Disclosure Bulletin, Vol. 34, No. 9, February 1992, p. 220.
V	AS	XP 000583029, Low Dielectric Constant Materials for Interlayer Dielectric Applications, Shyam P. Murarka, Solid State Technology, March 1996, No. 3, Tulsa, OK, US, pp 3-7.
V	AT	XP-000952344, Processing and Characterization of Silica Xerogel Films for Low-K Dielectric Applications, Anarag Jain, et al., Mat. Res. Soc. Symp. Proc. Vol. 565, 1999, Materials Research Society, pp 8-19.

EXAMINER

HUNG K VU

DATE CONSIDERED

07/10/01

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE U.S. PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO.: 30-4687 (4790)	SERIAL NO.: 09/328,646 RECEIVED
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			APPLICANT: SHI-QING WANG, ET AL	MAY 30 2001
MAY 21 2001 (Use several sheets if necessary)			FILING DATE: 06/09/01	GROUP: TECHNOLOGY CENTER 2800 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Vu	AA	5,858,869	01/12/1999	Chen, et al.	438	597	-
Vu	AB	6,080,526	06/27/2000	Yang, et al.	430	296	-
Vu	AC	6,097,095	08/01/2000	Chung	257	774	-
Vu	AD	6,124,198	09/26/2000	Moslehi	438	622	-
Vu	AE	6,143,641	11/07/2000	Kitch	438	618	-
Vu	AF	6,165,893	12/26/2000	Chung	438	623	-
Vu	AG	6,207,555	03/27/2001	Ross	438	633	-
Vu	AH	6,211,063	04/03/2001	Liu, et al.	438	624	-
	AI						
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
	AL						
	AM						
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	AP						
	AQ						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

Vu	AR	"HIGH STUD-TO-LINE CONTACT AREA IN DAMASCENE METAL PROCESSING", IBM TECHNICAL DISCLOSURE BULLETIN, VOL. 33, NO. 1A, JUNE 1990, PA. 160-161.
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EXAMINER HUNG K. VU

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U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
V	AA	5, 801,095	9/01/98	YEW, ET AL	438	624	-	
	AB							
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FOREIGN PATENT DOCUMENTS								
							TRANSLATION	
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
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	AN							
	AO							
	AP							
	AQ							
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)								
V	AR	"HIGH STUD-TO-LINE CONTACT AREA IN DAMASCENE METAL PROCESSING"; IBM TECHNICAL DISCLOSURE BULLETIN, VOL. 33, NO. 1A, JUNE 1990, PP. 160-161.						
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